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ОБРАЗОВАНИЕ, СТЕПЕНЬ

1977- 1983: Московский государственный университет, физический факультет, диплом физика.
1987-1990 : Аспирант в Ташкентском государственном университете
1993- Диплом кандидата физико-математических наук. (01.04.10- физика полупроводников)
2019- Диплом Доктора наук по специальности физика полупроводников (01.04.10)

ТРУДОВАЯ ДЕЯТЕЛЬНОСТЬ:

1983 – 1985: служба в армии
1985 – 1986: Младший научный сотрудник в лаборатории гамма-активационного анализа, Институт прикладной физики Ташкентского государственного университета.
1990 - 1992: инженер кафедры физики полупроводников и диэлектриков Ташкентского государственного университета
1992 - 1996: Ассистент кафедры физики Ургенчского государственного университета.
1997- 2010: Заведующий кафедрой физики, Ургенчский государственный университет .
2010- 2013: Заместитель директора Ургенчского филиала Ташкентского университета информационных технологий.
2013- 2016: Доцент кафедры естественных наук Ургенчского филиала Ташкентского университета информационных технологий.
2016- present: доцент кафедры физики, Ургенчский государственный университет

СПЕЦИАЛЬНОСТЬ

- Физика.

ПРЕПОДАВАЕМЫЕ ПРЕДМЕТЫ

- Квантовая механика, Моделирование полупроводниковых приборов, физические основы фотовольтаики

ОБЛАСТЬ НАУЧНЫХ ИНТЕРЕСОВ:

Моделирование полупроводниковых приборов, полупроводниковые многослойные структуры, МОП структуры, МОП транзисторы, FinFET транзисторы, беспереходные

	МОП транзисторы, короткоканальные эффекты в наноразмерных МОП транзисторах, случайные телеграфные шумы, радиационная физика полупроводниковых приборов.
ПРОЕКТЫ:	<p>2016-2019. RENES – “ Development of the Master program in renewable energy and sustainable environment” (Erasmus+ program).</p> <p>2017-2020. “ New approach to investigation of the nature and lateral distribution of the defects at Si-SiO₂ interface and in the oxide layer”. Ministry of innovational development of Uzbekistan.</p> <p>2021-2023. Совместный Индийско-Узбекский проект “Self Heating Effect on stacked Nanosheet Field Effect Transistor”</p>
ПУБЛИКАЦИИ	<p>1.Atamuratov A.E., Babadjanov R.D., Gromov Y.A., Zaynabidinov S. Influence of bremsstrahlung with Emax = 25 MeV on MOSFET characteristics. Doclady Physics 1989, No. 3, p. 31</p> <p>2. Zaynabidinov S., Daliev H., Atamuratov A.E. Low temperature annealing influence to the Si-SiO₂ interface states dencities of MOSFETs. Doclady Physics.1992, No.1, p.24.</p> <p>3. Atamuratov A.E., Zainabidinov S., Yusupov A., Daliev H.S., Adinaev K. Influence of surface states generated at the Si--SiO₂ interface to the MOSFET leakage current. Tech. Phys. Lett. Vol. 21, No.21, 79 (1995)</p> <p>4. Atamuratov A.E., Zainabidinov S., Daliev H.S., Yusupov A., Adinaev K. Effect of thermal--field treatment and ionizing radiation on the energy spectrum of Si-SiO₂ interface states of a MOSFET. Tech. Phys. Vol. 42, No.9, pp. 1106-1107 (1997)</p> <p>5. Zainabidinov S., Atamuratov A.E., Yusupov A., Adinaev K. Ionizing Radiations and annealing influence on MOSFET charge states. Tr. J. of Physics, V.23, No. 3, 1999, p.485.</p> <p>6. Atamuratov A.E., Yusupov A., Adinaev K. Experimental Assesment of the Nonuniform Radiation – Induced Space – Charge Distribution in the Surface Region of Silicon. Inorganic Materials, 2001, Vol. 37, No. 8, p.767.</p> <p>7. Atamuratov A.E., Yusupov A., Aminov U.A. Influence of a high energy Bremsstrahlung and heat treatment on parameters of the MOSFET. Informations of Higher Educational establishments. An electron technology materials, 2003, No.4, p. 54-56 (in Russian).</p> <p>15. A.E. Atamuratov. Influence of the high-energy bremsstrahlung on field transistor threshold voltage. Uzbek Journal of Physics, 2003, V.5(№5-6), pp.356-358.</p> <p>8. A.E.Atamuratov, H.-H. Wehmann. Determination of the longitudinal charge distribution at the Si-SiO₂ interface of MOSFET by C–V measurements;Materials of Second International Conference “ Fundamental and Applied Problems of Physics”, Tashkent (2004), p.222-224 .</p> <p>9. A. E. Atamuratov, A. Yusupov, K. Babajanov . Distribution of surface carrier concentration in the cylindrical MOSFET with the built-in charge in oxide layer. Materials of Republican conference on Physical Electronics, Tashkent, November 2-4 (2005), p. 48 (in Russian).</p>

- 10.** A. E. Atamuratov, Charulata Barge, H.-H Wehmann. Features of the charged area image on a SiO₂ surface. Materials of Conference “Fundamental and Applied Problems of Physics”, Tashkent (2006), p. 146-148.
- 11.** A. E. Atamuratov, D. U. Matrasulov, and P. K. Khabibullaev. Detection of a Charge Built in Oxide Layer of a Metal–Oxide–Semiconductor Field-Effect Transistor by Lateral C- V Measurement. Doklady Physics, 2007, Vol. 52, No. 6, pp. 322–325.
- 12.** A.E. Atamuratov. Modeling of quantum wires in the interface layer of the semiconductor-oxide structures with charge built in oxide. Complex Phenomena in Nanoscale Systems.NATO Science for Peace and Security Series-B:Physics and Biophysics. Proceedings of the NATO Advanced Research Workshop on Recent Advances in Nonlinear Dynamics and Complex System Physics; From natural to Social Sciences and Security. Tashkent, Uzbekistan, 12-17 October 2008, p.229-237.
- 13.** A. N. Georgobiani , A. E. Atamuratov , U. A. Aminov , and T. A. Atamuratov. Tunable SiO₂/Si-Based Nanostructures. Inorganic Materials, 2009, Vol. 45, No. 8, pp. 900–904.
- 14.** A. E. Atamuratov, D. Yu. Matrasulov, and P. K. Khabibullaev. Influence of the Field of the Built_in Oxide Charge on the Lateral C–V Dependence of the MOSFET. Doklady Physics, 2010, Vol. 55, No. 2, pp. 52–54.
- 15.** J. D. Wei, S. F. Li, A. Atamuratov, H.-H. Wehmann, and A. Waag . Photoassisted Kelvin probe force microscopy at GaN surfaces: The role of polarity. Appl. Phys. Lett. **97**, 172111 (2010).
- 16.** A.E. Atamuratov, R. Granzner , M. Kittler, Z. Atamuratova, M. Halillaev, F. Schwierz . Simulation of Random Telegraph Noise in nanometer nMOSFET induced by interface and oxide trapped charge. NATO Advanced Research Workshop on Low Dimensional Functional Materials, October 15-19, 2012, Tashkent
- 17.** A.E. Atamuratov , Z. Atamuratova, M. Halillaev, G. Ghione. Simulation of carrier distribution in nanometer MNOSFET with single charge trapped in oxide and at SiO₂ – Si₃N₄ interface. Materials of International conference Low dimensional nanoscale systems: quantum effects, particle transport and advanced materials. November 6-7,2012, Tashkent.
- 18.** Matyakubov H., Atamuratova Z. A., Abdikarimov A., Halillaev M., Atamuratov A.E. The method of estimation of single trapped charge position in nanometer MNOSFET oxide layer and Si-SiO₂ interface. Materials of International conference Fundamental and Applied Problems of Physics November 14-16,2013, Tashkent.
- 19.** A. Abdikarimov, G.Indalecio, E. Comesana, N. Seoane, K. Kalna, A.J. Garcia-Lourero, A. E. Atamuratov. Influence of device geometry on electrical characteristics of a 10.7 nm SOI-FINFET.in 17th International Workshop on Computational Electronics. IWCE 2014. pp.1-4. [Online]. Available: <http://ieeexplore.ieee.org/xpl/articleDetails.jsp?reload=true&arnumber=6865877>
- 20.** A.E.Atamuratov, U.A.Aminov, Z.A. Atamuratova, M. Halillaev, A. Abdikarimov , H. Matyakubov. The lateral capacitance of nanometer MNOSFET with a single charge

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22. A. Abdikarimov, A.E. Atamuratov, A. Yusupov, Simulation study of subthreshold slope in 25 nm SOI-FinFET with the different body shape. Simulation of DIBL effect in junctionless SOI MOSFETs with extended gate. *Doclady Uzb Academy N 3*, p.20-22, 2017.
23. A. E. Atamuratov, M. Khalilloev, A. Abdikarimov, Z.A. Atamuratova, M. Kittler, R. Granzner, F. Schwierz, Influence of non-uniform lateral interface defects distribution to the current-voltage characteristic of MOSFET. *Nanosystems: physics, chemistry, mathematics*, 2017, 8 (1), p. 75–78.
24. Atamuratov A.E., Abdikarimov A., Atamuratova Z.A., Xolillaev M., Yusupov A. Collection of papers (Urgench state university). Actual problems of modern science, education and training in the region 8-12 page, N1, 2017
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27. Z. A. Atamuratova, A. Yusupov, B. O. Khalikberdiev, and A. E. Atamuratov Anomalous Behavior of Lateral C–V Characteristic of an MNOS Transistor with an Embedded Local Charge in the Nitride Layer. *Technical Physics*, 2019, Vol. 64, No. 7, pp. 1006–1009.
28. Atabek E. Atamuratov 1, Mahkam M. Khalilloev, Ahmed Yusupov, A. J. Garcia-Loureiro, Jean Chamberlain Chedjou and Kyamakya Kyandoghere. Contribution to the Physical Modelling of Single Charged Defects Causing the Random Telegraph Noise in Junctionless FinFET. *Appl. Sci.* 2020, 10(15), 5327; doi:10.3390/app10155327
29. Ahmed Yusupov, Atabek E. Atamuratov, Azamat E. Abdikarimov, Jean Chamberlain Chedjou and Kyandoghere Kyamakya. The amplitude of RTN in nanometer SOI FinFET with different channel shape. *World Scientific Proceedings Series on Computer Engineering and Information Science Developments of Artificial Intelligence Technologies in Computation and Robotics*, pp. 1541-1548 (2020).
30. Atabek E. Atamuratov, Ahmed Yusupov, Zuhra A. Atamuratova, Jean Chamberlain Chedjou and Kyamakya Kyandoghere. Lateral Capacitance–Voltage Method of NanoMOSFET for Detecting the Hot Carrier Injection. *Appl. Sci.* 2020, 10(21), 7935; doi:10.3390/app10217935